

30V, 40A, 10.6mΩ Dual N-channel Power Trench MOSFET

JMTQ3400D

Features

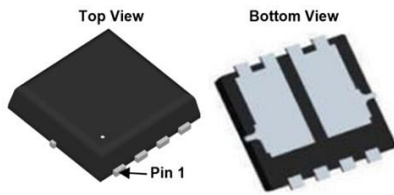
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

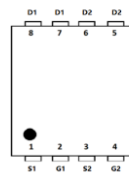
- Load Switch
- PWM Application
- Power Management

Product Summary

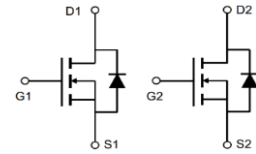
Parameters	Value	Unit
V_{DSS}	30	V
$V_{GS(th)}_{Typ}$	1.0	V
$I_D(@V_{GS}=10V)$	40	A
$R_{DS(ON)}_{Typ}(@V_{GS}=10V)$	10.6	mΩ
$R_{DS(ON)}_{Typ}(@V_{GS}=4.5V)$	11.3	mΩ



PDFN3x3-8L-D



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTQ3400D	Q3400D	1	Tape&Reel	PDFN3x3-8L-D	5000	50000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	40
		$T_C = 100^\circ\text{C}$	25
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	31	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	40
		$T_C = 100^\circ\text{C}$	16
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	52	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.1	

**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 12\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	0.7	1.0	1.3	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}$, $I_D = 4.2\text{A}$	-	10.6	13.8	m Ω
		$V_{GS} = 4.5\text{V}$, $I_D = 4\text{A}$	-	11.3	14.7	m Ω
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	1.0	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 15\text{V}$, $f = 1\text{MHz}$	1095	1533	2069	pF
C_{oss}	Output Capacitance		84	118	160	pF
C_{riss}	Reverse Transfer Capacitance		67	94	126	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 10V $V_{DS} = 15\text{V}$, $I_D = 6\text{A}$	11	16	21	nC
Q_{gs}	Gate Source Charge		-	3.3	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	3.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}$, $V_{DD} = 15\text{V}$ $I_D = 6\text{A}$, $R_{GEN} = 3\Omega$	-	10	-	ns
t_r	Turn-On Rise Time		-	23	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	33	-	ns
t_f	Turn-Off Fall Time		-	6.8	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	40	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	159	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 4.5\text{A}$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 4.2\text{A}$, $di/dt = 100\text{A/us}$	9	12	17	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	5.2	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 15\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 250\text{ohm}$, $L = 0.5\text{mH}$, $I_{AS} = 11.2\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

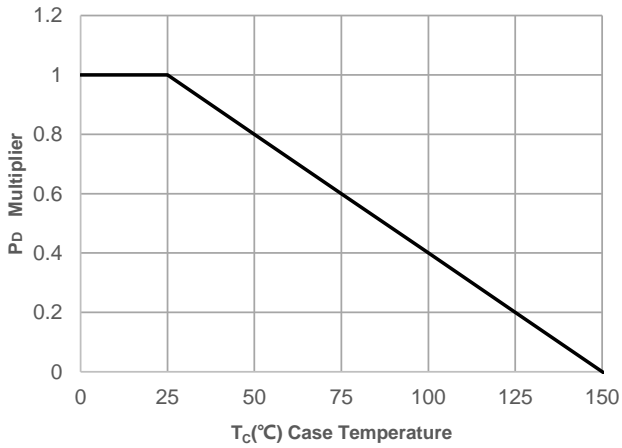


Figure 2: Current De-rating

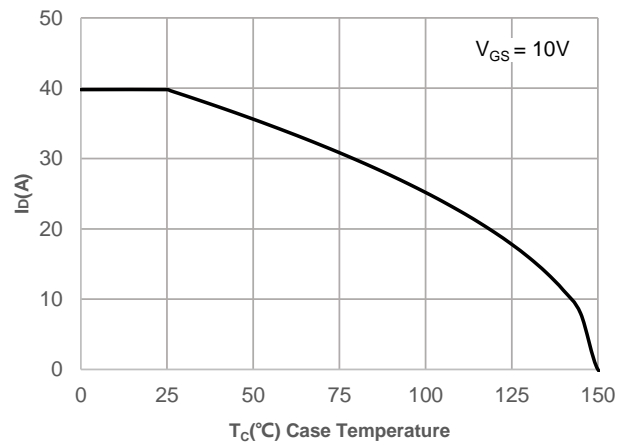


Figure 3: Normalized Maximum Transient Thermal Impedance

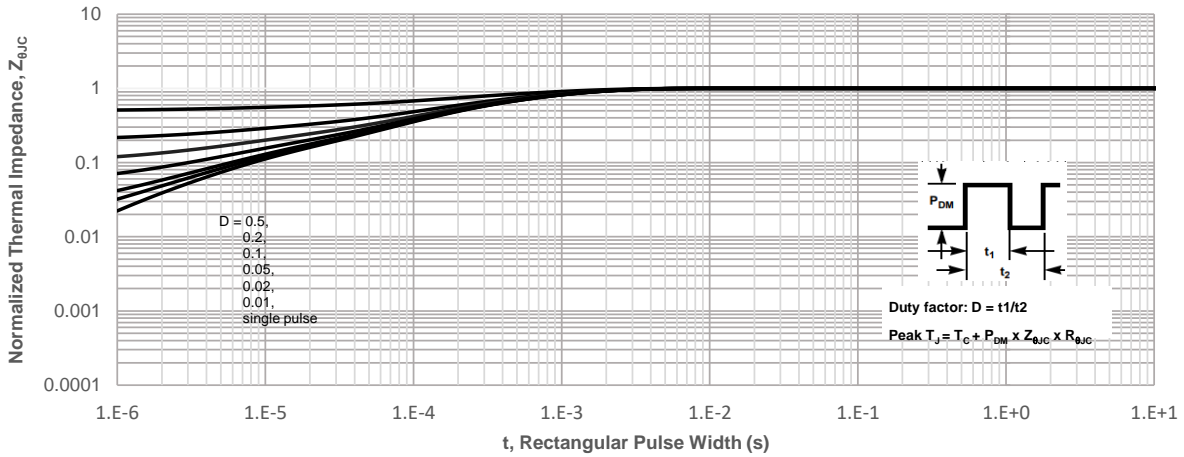
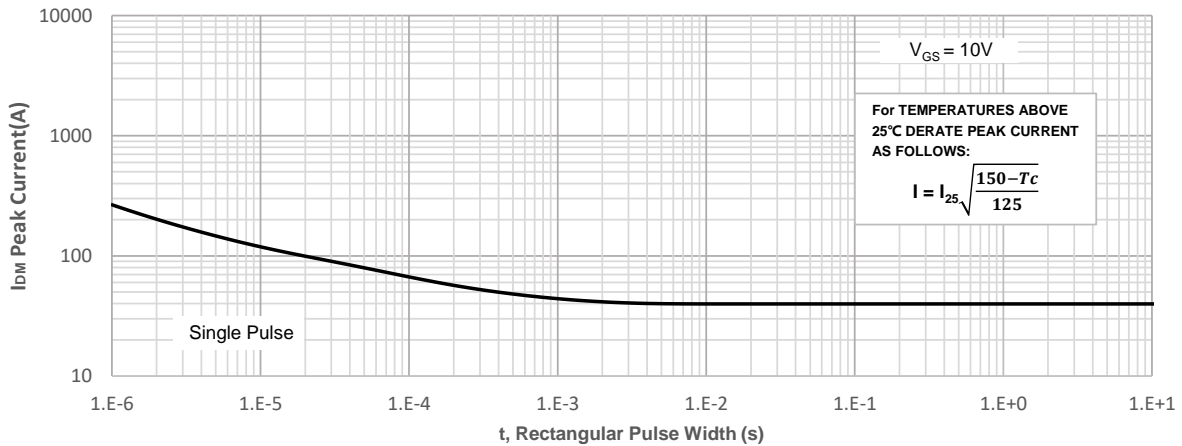
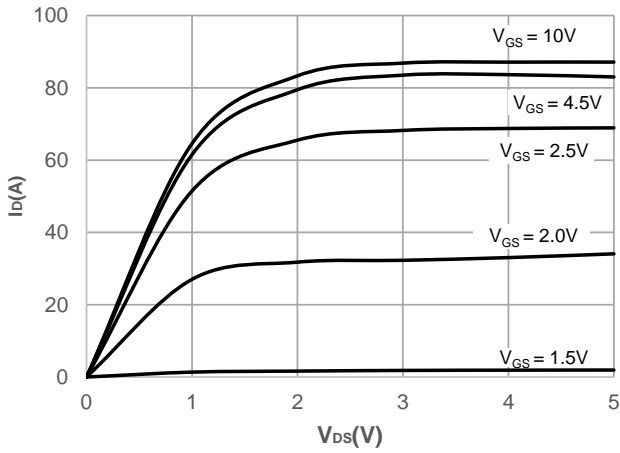
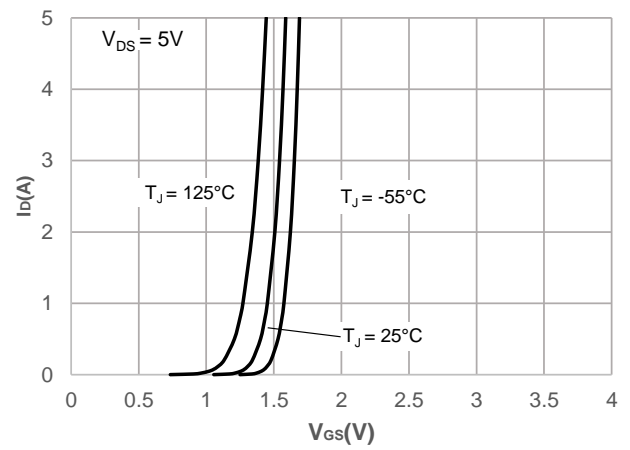
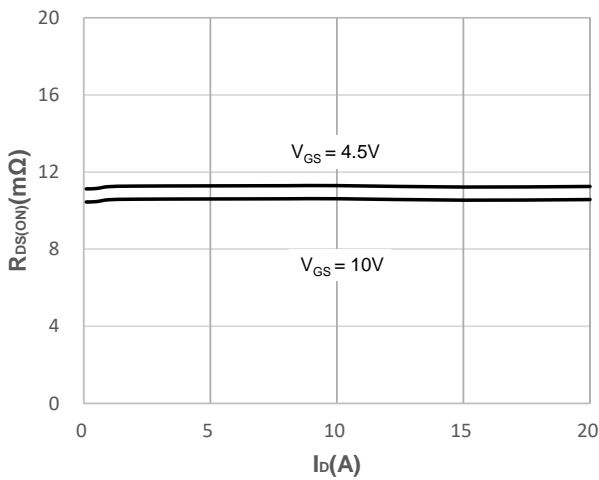
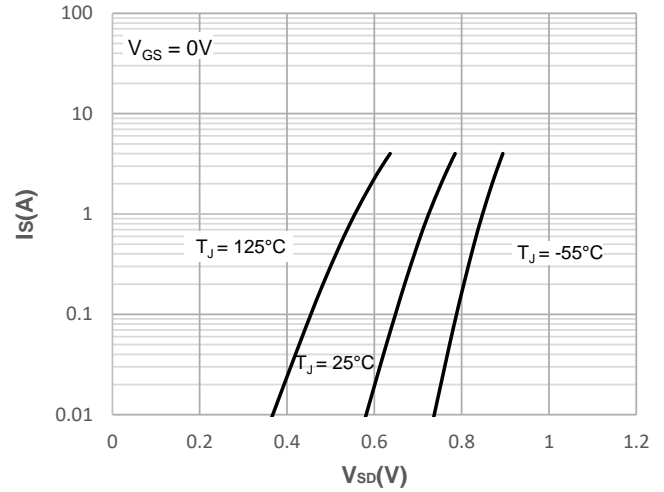
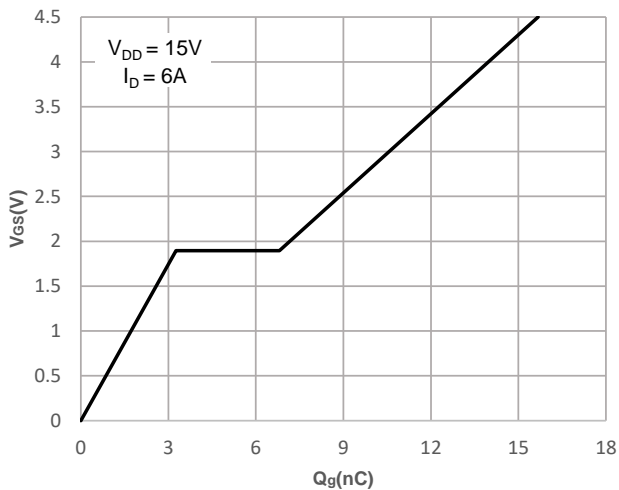
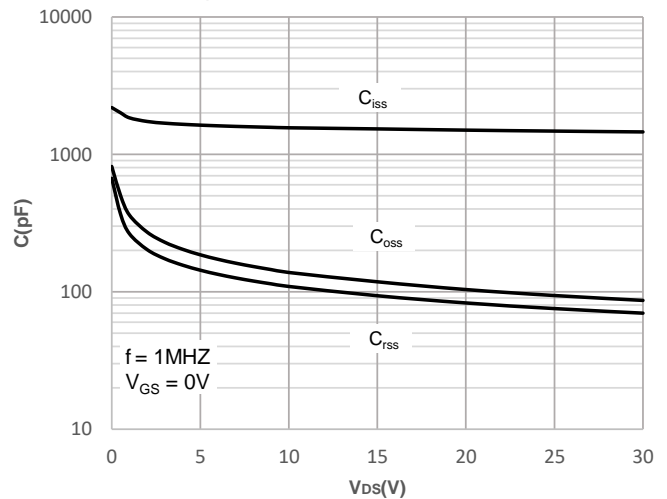


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

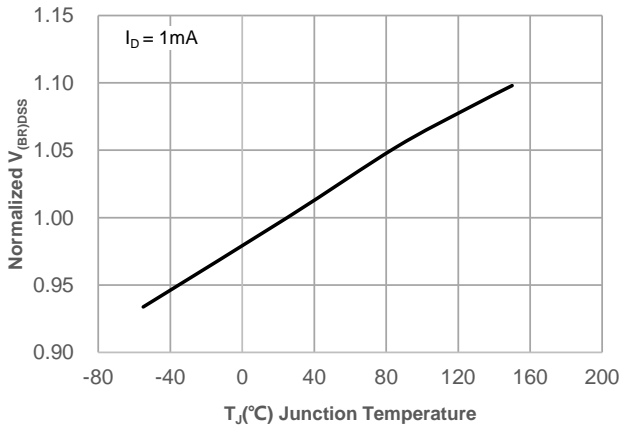


Figure 12: Normalized on Resistance vs. Junction Temperature

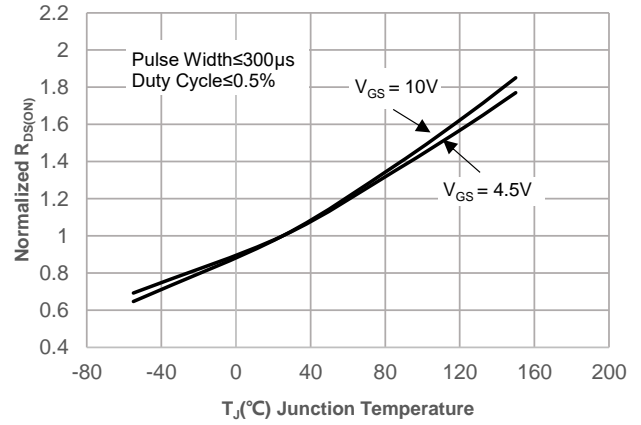


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

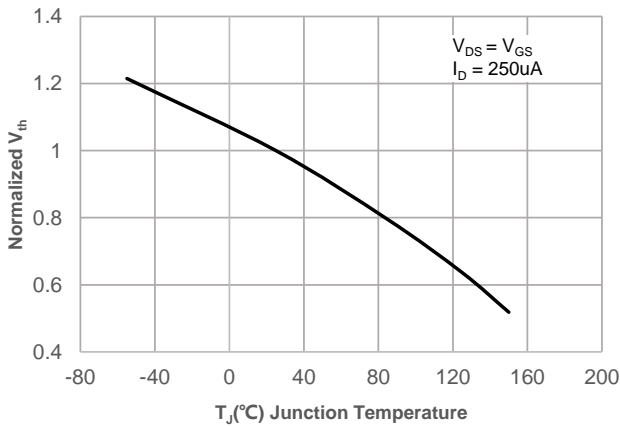


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

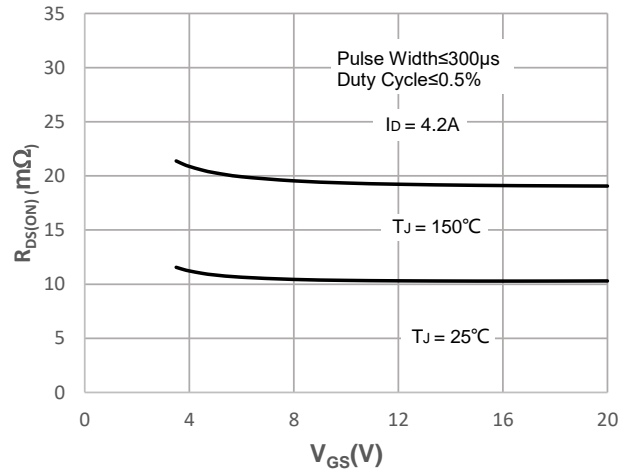
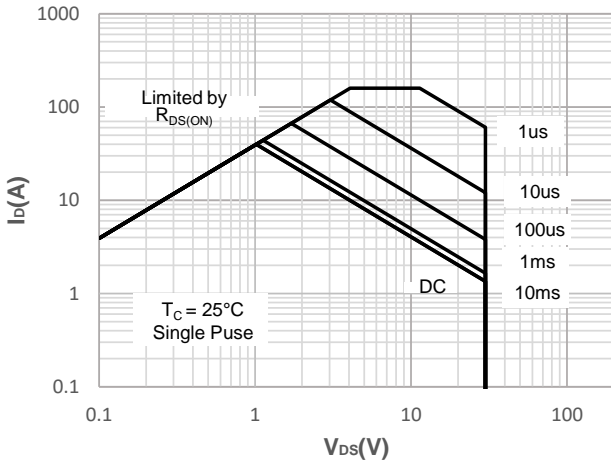


Figure 15: Maximum Safe Operating Area



Test Circuit

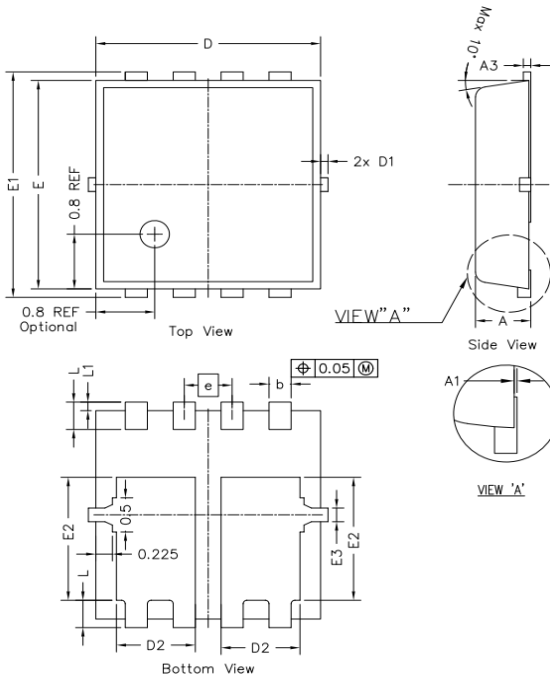
Figure 1: Gate Charge Test Circuit & Waveform

Figure 2: Resistive Switching Test Circuit & Waveform

Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

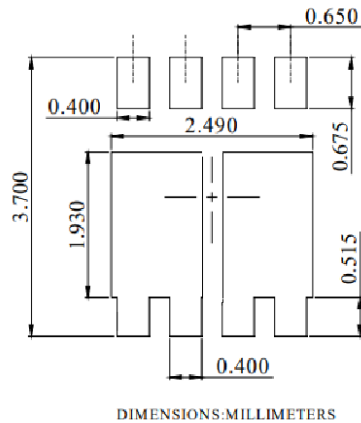
Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN3X3-8L-D)



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	---	---	0.050	----	----	0.002
A3	0.144	0.152	0.202	0.006	0.006	0.008
b	0.250	0.300	0.350	0.010	0.012	0.014
e	0.65 BSC			0.026 BSC		
D	2.950	3.050	3.150	0.116	0.120	0.124
E	2.950	3.050	3.150	0.116	0.120	0.124
D1	---	---	0.125	----	----	0.005
E1	3.200	3.300	3.400	0.126	0.130	0.134
D2	0.970	1.070	1.170	0.038	0.042	0.046
E2	1.700	1.800	1.900	0.067	0.071	0.075
E3	0.150	0.200	0.250	0.006	0.008	0.010
L	0.300	0.400	0.500	0.012	0.016	0.020
L1	0.075	0.125	0.175	0.003	0.005	0.007

Recommended Soldering Footprint



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